

Product Summary

$V_{(BR)DSS}$	$R_{DS(on) \max}$	I_D $T_A = 25^\circ\text{C}$
60V	44m Ω @ $V_{GS} = 10\text{V}$	5.0A
	60m Ω @ $V_{GS} = 4.5\text{V}$	4.3A

Description and Applications

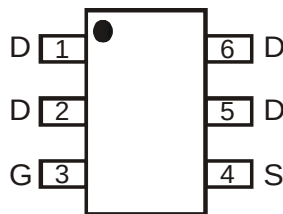
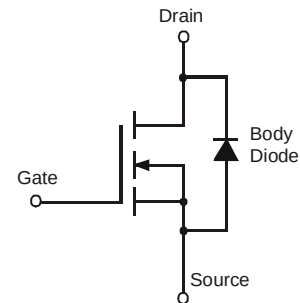
This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- DC-DC Converters
- Power management functions
- Backlighting

TSOT26



Top View


 Top View
Pin Configuration


Equivalent Circuit

Features and Benefits

- 100% Unclamped Inductive Switch (UIS) test in production
- Low Input Capacitance
- Low On-Resistance
- Fast Switching Speed
- **Lead, Halogen, and Antimony Free, RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

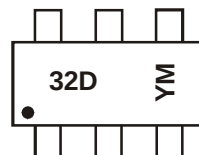
- Case: TSOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Tin Finish annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.013 grams (approximate)

Ordering Information (Note 3)

Part Number	Case	Packaging
DMN6040SVT-7	TSOT26	3,000/Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. No purposely added lead. Halogen and Antimony free.
 2. Diodes Inc.'s "Green" policy can be found on our website at <http://www.diodes.com>.
 3. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information



32D = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: X = 2010)
 M = Month (ex: 9 = September)

Date Code Key

Date Code Key

Year	2010	2011	2012	2013	2014	2015	2016
Code	X	Y	Z	A	B	C	D

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	60	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 5) V _{GS} = 10V	Steady State	T _A = 25°C T _A = 70°C	I _D	5.0 4.0	A
	t < 10s	T _A = 25°C T _A = 70°C	I _D	6.3 5.0	A
Continuous Drain Current (Note 5) V _{GS} = 5V	Steady State	T _A = 25°C T _A = 70°C	I _D	4.3 3.4	A
	t < 10s	T _A = 25°C T _A = 70°C	I _D	5.4 4.3	A
Maximum Body Diode Forward Current (Note 5)			I _S	2.1	A
Pulsed Drain Current (10μs pulse, duty cycle = 1%)			I _{DM}	30	A
Avalanche Current (Note 6) L = 0.1mH			I _{AR}	14.2	A
Avalanche Energy (Note 6) L = 0.1mH			E _{AR}	10	mJ

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 4)	T _A = 25°C	P _D	1.2	W
	T _A = 70°C		0.75	
Thermal Resistance, Junction to Ambient (Note 4)	Steady state	R _{θJA}	106	°C/W
	t < 10s		69	°C/W
Total Power Dissipation (Note 5)	T _A = 25°C	P _D	1.8	W
	T _A = 70°C		1.1	
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	R _{θJA}	68	°C/W
	t < 10s		44	°C/W
Thermal Resistance, Junction to Case (Note 5)		R _{θJC}	20	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

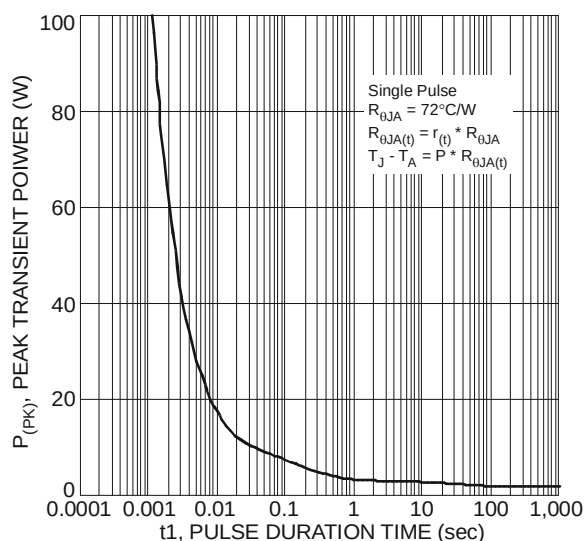


Fig. 1 Single Pulse Maximum Power Dissipation

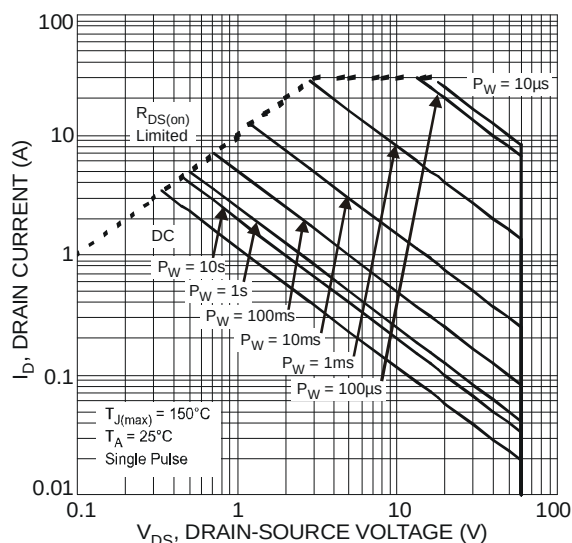


Fig. 2 SOA, Safe Operation Area

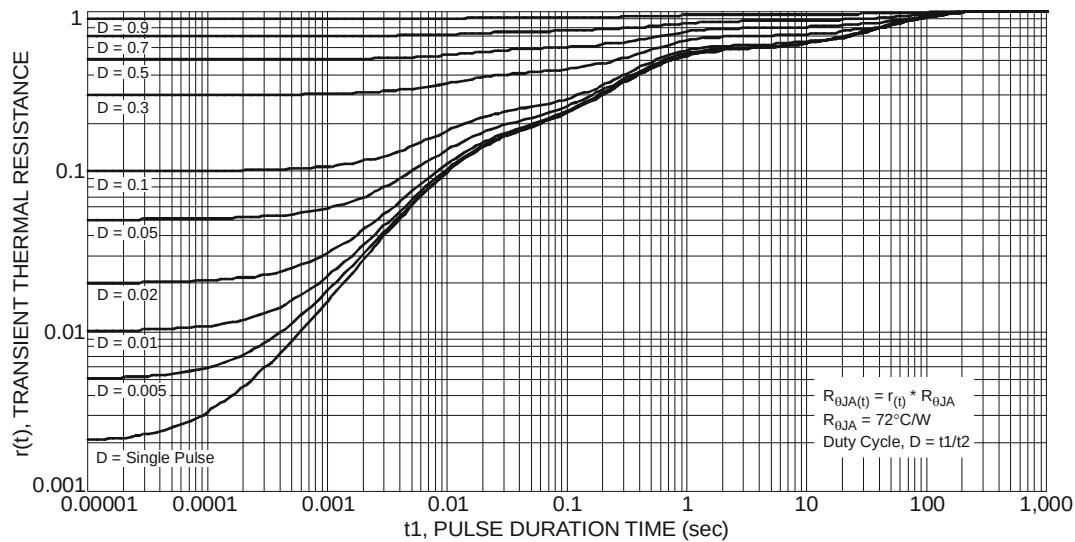


Fig. 3 Transient Thermal Resistance

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	100	nA	V _{DS} = 60V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	1	—	3	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(on)}	—	30	44	mΩ	V _{GS} = 10V, I _D = 4.3A
		—	35	60		V _{GS} = 4.5V, I _D = 4A
Forward Transfer Admittance	Y _{fs}	—	4.5	—	S	V _{DS} = 10V, I _D = 4.3A
Diode Forward Voltage	V _{SD}	—	0.7	1.2	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	1287	—	pF	V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	57	—		
Reverse Transfer Capacitance	C _{rss}	—	44	—		
Gate Resistance	R _G	—	1.2	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = 10V)	Q _g	—	22.4	—	nC	V _{DS} = 30V, I _D = 4.3A
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	10.4	—		
Gate-Source Charge	Q _{gs}	—	4.9	—		
Gate-Drain Charge	Q _{gd}	—	3.0	—		
Turn-On Delay Time	t _{D(on)}	—	6.6	—	nS	V _{GS} = 10V, V _{DD} = 30V, R _G = 6Ω, I _D = 4.3A
Turn-On Rise Time	t _r	—	8.1	—		
Turn-Off Delay Time	t _{D(off)}	—	20.1	—		
Turn-Off Fall Time	t _f	—	4.0	—		
Body Diode Reverse Recovery Time	t _{rr}	—	18	—	nS	I _S = 4.3A, dI/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q _{rr}	—	11.9	—	nC	I _S = 4.3A, dI/dt = 100A/μs

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - I_{AR} and E_{AR} rating are based on low frequency and duty cycles to keep T_J = 25°C
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

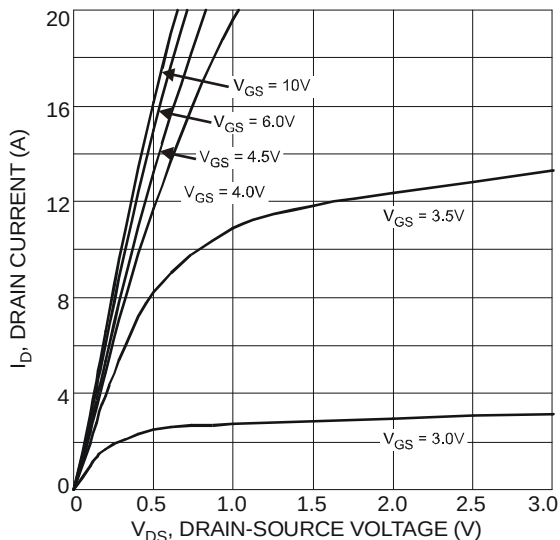


Fig. 4 Typical Output Characteristic

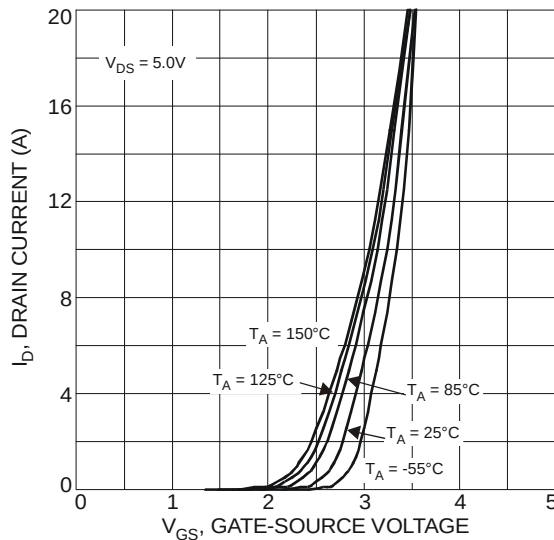


Fig. 5 Typical Transfer Characteristics

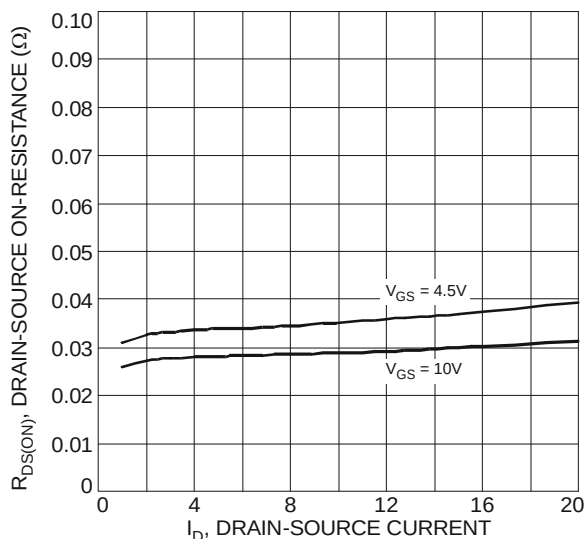


Fig. 6 Typical On-Resistance vs. Drain Current and Gate Voltage

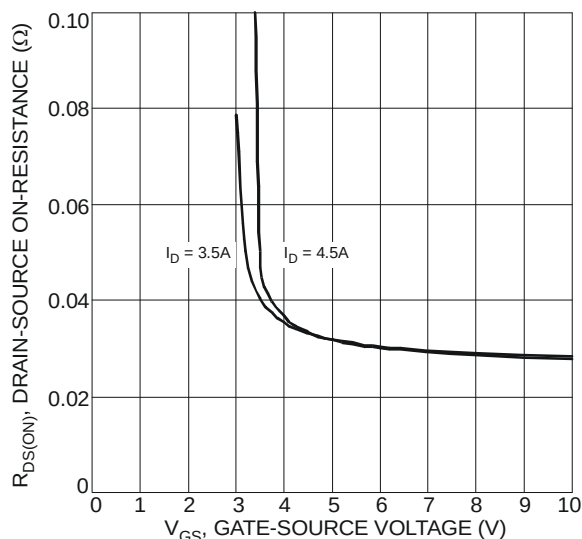


Fig. 7 Typical On-Resistance vs. Drain Current and Gate Voltage

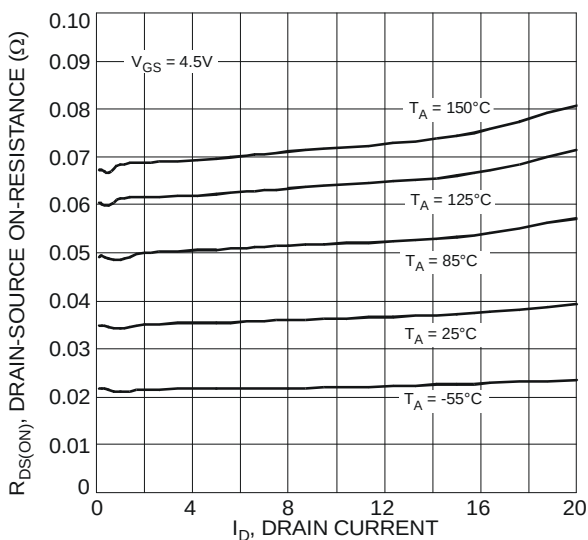


Fig. 8 Typical On-Resistance vs. Drain Current and Temperature

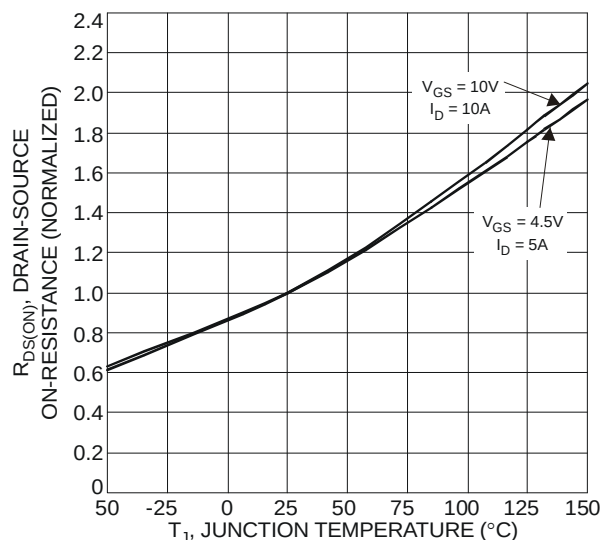


Fig. 9 On-Resistance Variation with Temperature

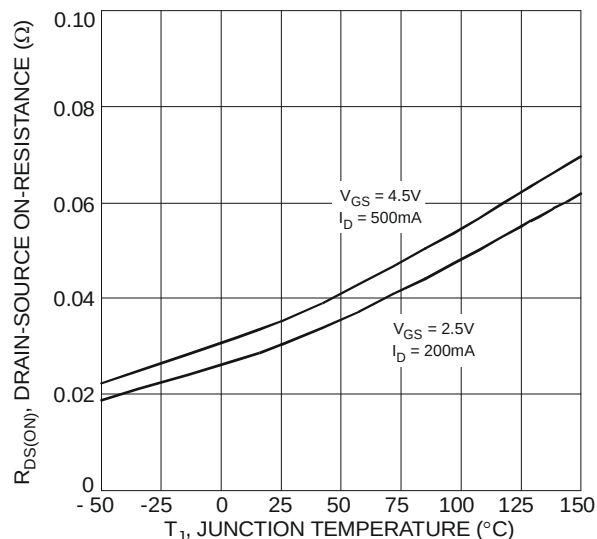


Fig. 10 On-Resistance Variation with Temperature

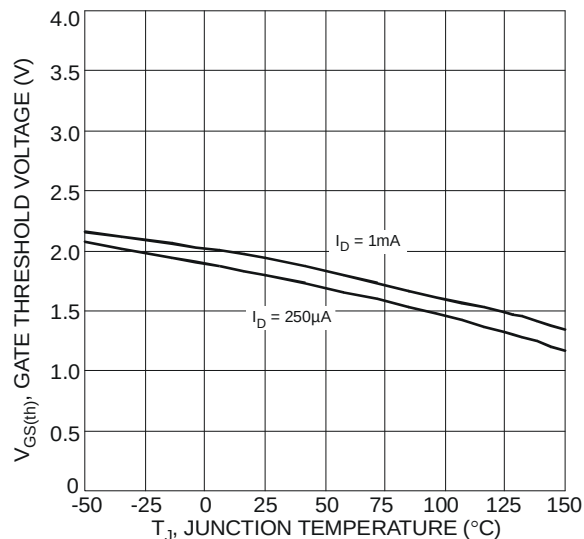


Fig. 11 Gate Threshold Variation vs. Ambient Temperature

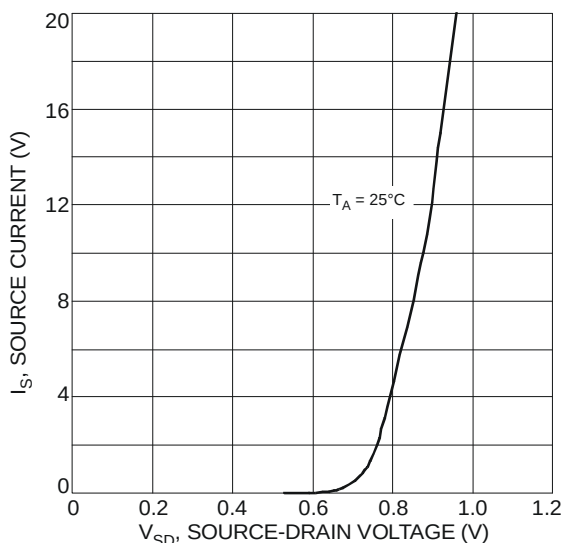


Fig. 12 Diode Forward Voltage vs. Current

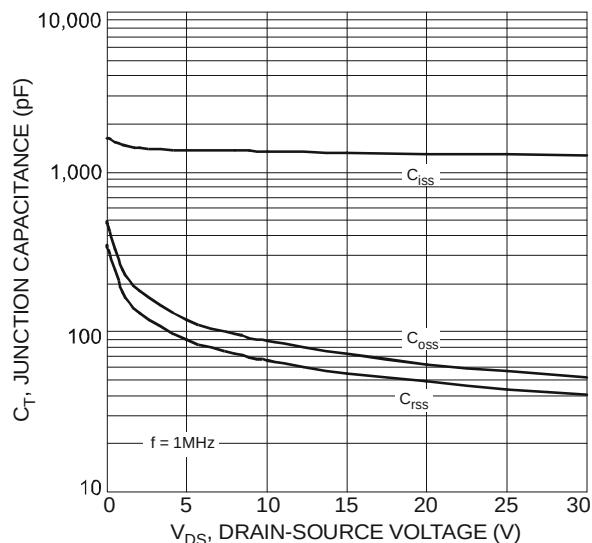


Fig. 13 Typical Junction Capacitance

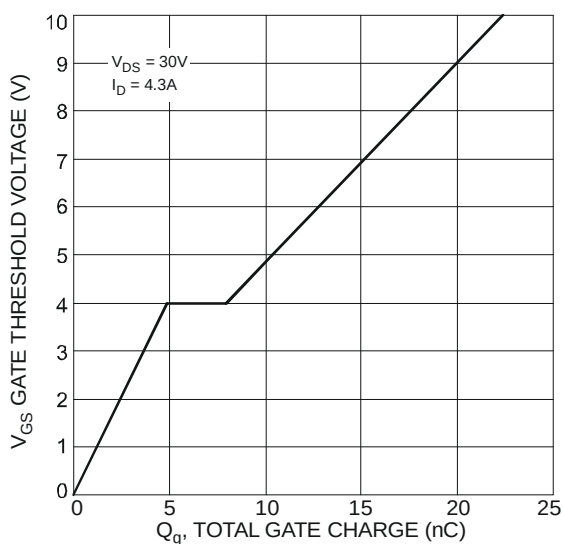
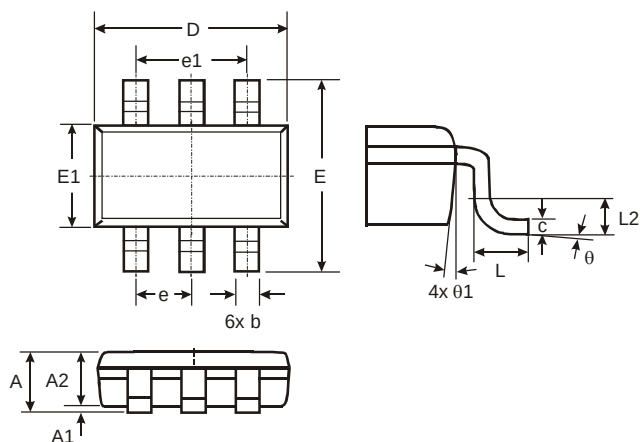


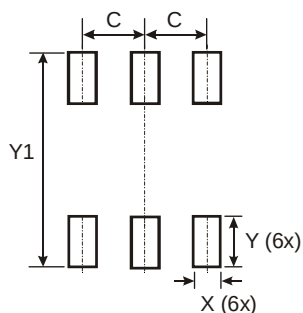
Fig. 14 Gate Charge

Package Outline Dimensions



TSOT26			
Dim	Min	Max	Typ
A	—	1.00	—
A1	0.01	0.10	—
A2	0.84	0.90	—
D	—	—	2.90
E	—	—	2.80
E1	—	—	1.60
b	0.30	0.45	—
c	0.12	0.20	—
e	—	—	0.95
e1	—	—	1.90
L	0.30	0.50	—
L2	—	—	0.25
θ	0°	8°	4°
θ_1	4°	12°	—
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
C	0.950
X	0.700
Y	1.000
Y1	3.199

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